

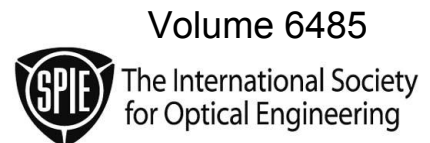
PROCEEDINGS OF SPIE

Novel In-Plane Semiconductor Lasers VI

Carmen Mermelstein
David P. Bour
Chairs/Editors

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